

Peak pulse voltage ($T_j=25$; non-repetitive, off-state; FIG.8)	V_{pp}	4	kV
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ELECTRICAL CHARACTERISTICS ($T_j=25$ unless otherwise specified)

Symbol	Test Condition	Quadrant	Value		Unit
I_{GT}	$V_D=12V$ $R_L=33$	- -	MAX.	35	mA
V_{GT}		- -	MAX.	1	V
V_{GD}	$V_D=V_{DRM}$ $T_j=150$ $R_L=3.3k$	- -	MIN.	0.2	V
I_L	$I_G=1.2I_{GT}$	-	MAX.	50	mA
				60	
I_H	$I_T=100mA$		MAX.	35	mA
dV/dt	$V_D=540V$ Gate Open $T_j=150$		MIN.	1200	V/ μs
$(dI/dt)_c$	$(dV/dt)_c=20V/\mu s$, $T_j=150$		MIN.	8	A/ms
t_{on}	$I_G=40mA$ $I_A=200mA$ $I_R=20mA$ $T_j=25$		TYP.	3	μs
t_{off}				30	

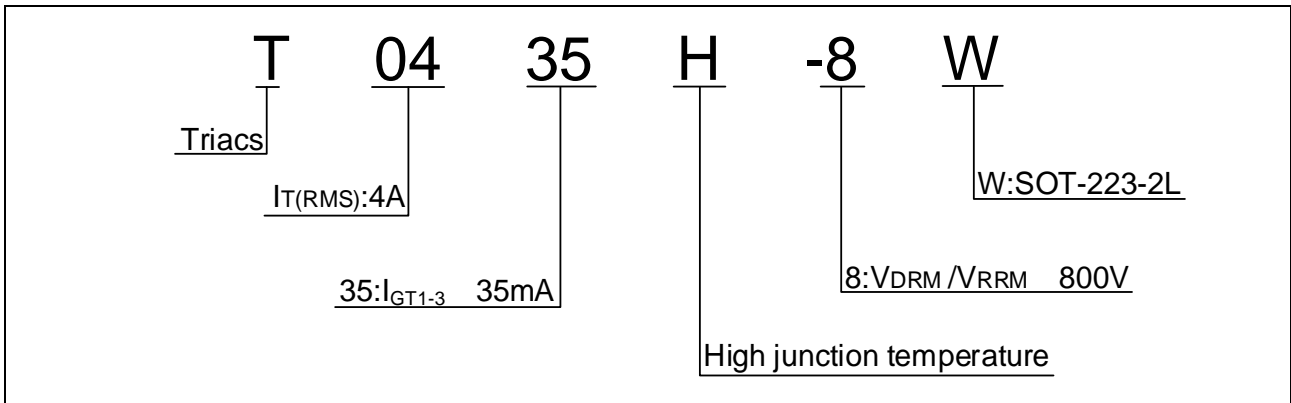
STATIC CHARACTERISTICS

Symbol	Parameter		Value(MAX.)	Unit
V_{TM}	$I_{TM}=5A$ $t_p=380\mu s$	$T_j=25$	1.5	V
V_{TO}	Threshold voltage	$T_j=150$	0.63	V
R_D	Dynamic resistance	$T_j=150$	324	m
I_{DRM}	$V_D=V_{DRM}$ $V_R=V_{RRM}$	$T_j=25$	5	μA
I_{RRM}		$T_j=150$	1	mA

THERMAL RESISTANCES

Symbol	Parameter	Value	Unit
$R_{th(j-c)}$	junction to case (AC)	17	$^{\circ}W$
$R_{th(j-a)}$	junction to ambient (AC)	60	$^{\circ}W$

ORDERING INFORMATION



MARKING

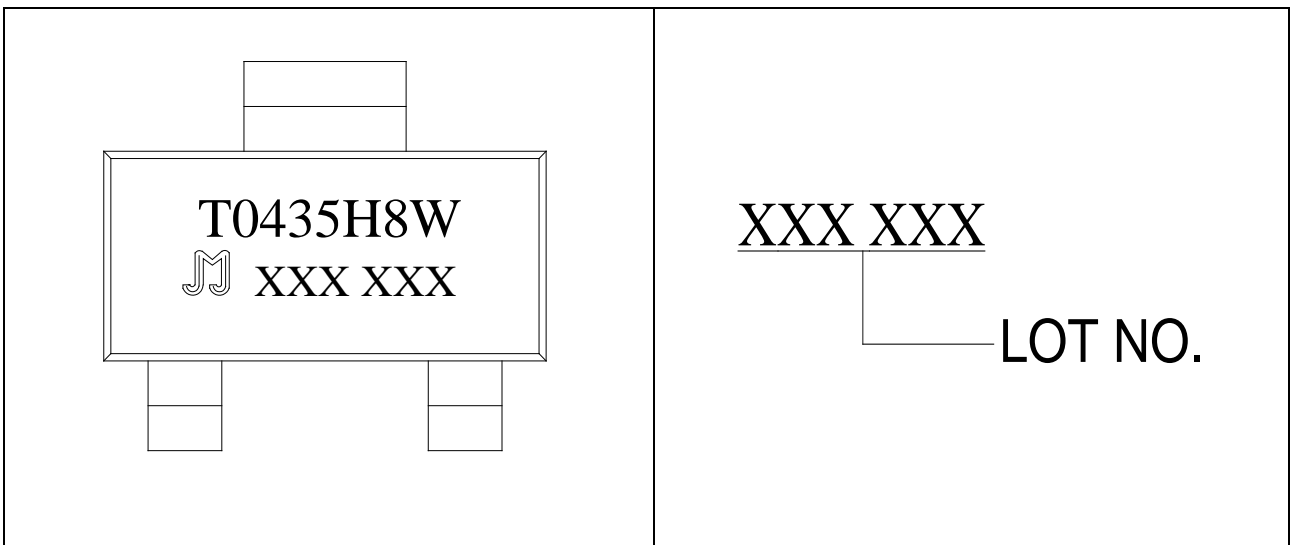


FIG.1: Maximum power dissipation versus RMS on-state current

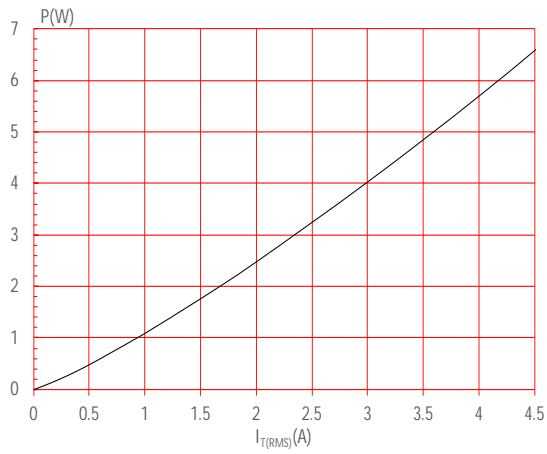


FIG.2: RMS on-state current versus case temperature

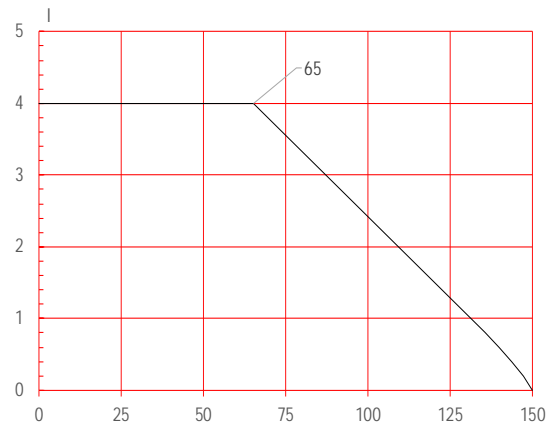


FIG.7: Relative variations of gate trigger current, holding current and latching current versus junction temperature

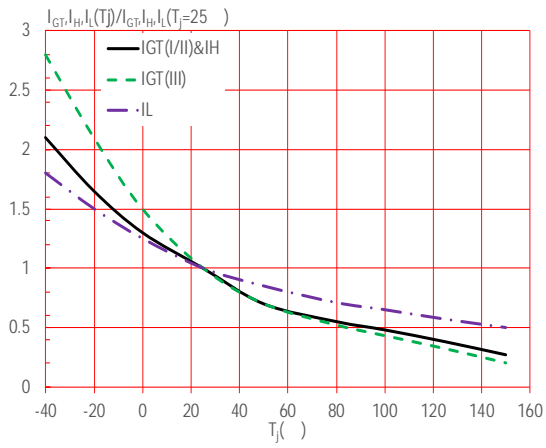
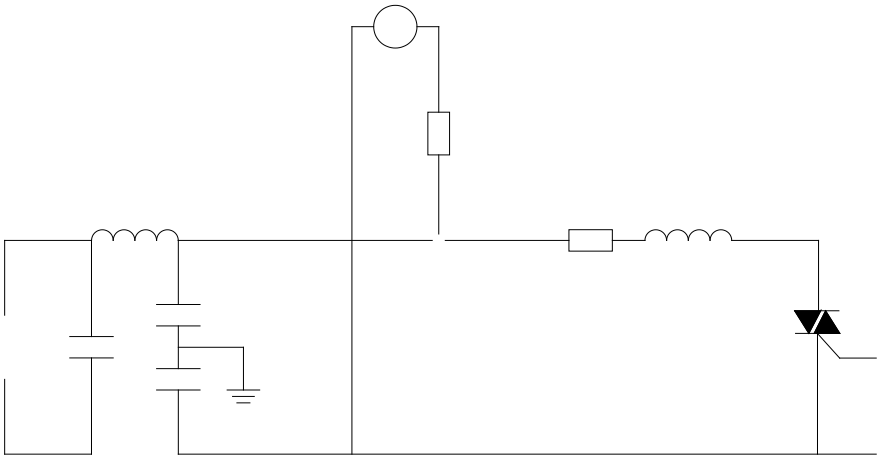


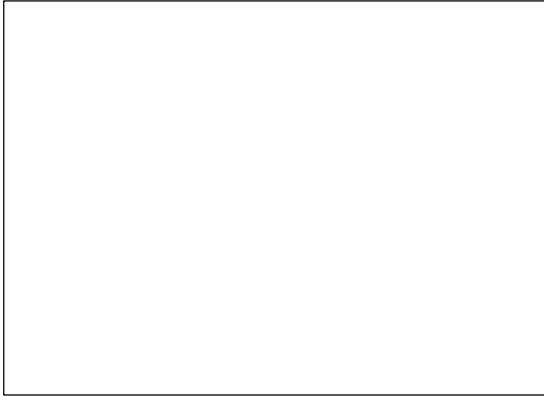
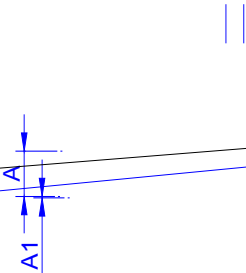
FIG.8 Test circuit for inductive and resistive loads to IEC-61000-4-5 standards



T0435H-8W

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PACKAGE MECHANICAL DATA



T0435H-8W

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